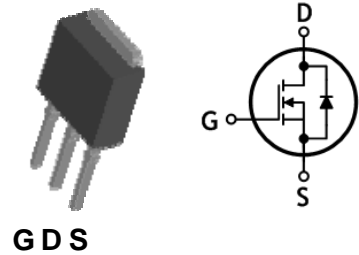


## SWITCHING REGULATOR APPLICATION

### Features

- $BV_{DSS}=800V$  Min.
- Low gate charge:  $Q_g=19nC$  (Typ.)
- Low drain-source On resistance:  $R_{DS(on)}=4.2\Omega$  (Max.)
- RoHS compliant device
- 100% avalanche tested



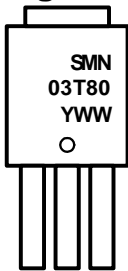
G D S

I-PAK

### Ordering Information

Part Number	Marking	Package
SMN03T80IS	SMN03T80	I-PAK (Short Lead)

### Marking Information



Column 1, 2: Device Code  
 Column 3: Production Information  
 e.g.) YWW  
 -. YWW: Date Code (year, week)

### Absolute maximum ratings ( $T_c=25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	$V_{DSS}$	800	V	
Gate-source voltage	$V_{GSS}$	$\pm 30$	V	
Drain current (DC) *	$I_D$	$T_c=25^\circ C$	3	A
		$T_c=100^\circ C$	1.83	A
Drain current (Pulsed) *	$I_{DM}$	12	A	
Single pulsed avalanche energy <sup>(Note 2)</sup>	$E_{AS}$	200	mJ	
Repetitive avalanche current <sup>(Note 1)</sup>	$I_{AR}$	3	A	
Repetitive avalanche energy <sup>(Note 1)</sup>	$E_{AR}$	7	mJ	
Power dissipation	$P_D$	70	W	
Peak diode recovery dv/dt <sup>(Note 3)</sup>	dv/dt	4.5	V/ns	
Junction temperature	$T_J$	150	$^\circ C$	
Storage temperature range	$T_{stg}$	-55~150	$^\circ C$	

\* Limited only maximum junction temperature

## Thermal Characteristics

Characteristic	Symbol	Rating	Unit
Thermal resistance, junction to case	$R_{th(j-c)}$	Max. 1.78	°C/W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	Max. 110	

## Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	$BV_{DSS}$	$I_D=250\mu\text{A}$ , $V_{GS}=0$	800	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}$ , $V_{DS}=V_{GS}$	2	-	4	V
Drain-source cut-off current	$I_{DSS}$	$V_{DS}=800\text{V}$ , $V_{GS}=0\text{V}$	-	-	10	$\mu\text{A}$
		$V_{DS}=640\text{V}$ , $T_C=125^\circ\text{C}$	-	-	100	$\mu\text{A}$
Gate leakage current	$I_{GSS}$	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 30\text{V}$	-	-	$\pm 100$	nA
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$ , $I_D=1.5\text{A}$	-	3.36	4.2	$\Omega$
Forward transfer conductance (Note 4)	$g_{fs}$	$V_{DS}=30\text{V}$ , $I_D=1.5\text{A}$	-	3.7	-	S
Input capacitance	$C_{iss}$	$V_{DS}=25\text{V}$ , $V_{GS}=0\text{V}$ , $f=1.0\text{MHz}$	-	696	-	pF
Output capacitance	$C_{oss}$		-	65	-	
Reverse transfer capacitance	$C_{rss}$		-	10.2	-	
Turn-on delay time (Note 4,5)	$t_{d(on)}$	$V_{DD}=400\text{V}$ , $I_D=3\text{A}$ $R_G=25\Omega$	-	48	-	ns
Rise time (Note 4,5)	$t_r$		-	36	-	
Turn-off delay time (Note 4,5)	$t_{d(off)}$		-	106	-	
Fall time (Note 4,5)	$t_f$		-	41	-	
Total gate charge (Note 4,5)	$Q_g$	$V_{DS}=640\text{V}$ , $V_{GS}=10\text{V}$ $I_D=3\text{A}$	-	19	-	nC
Gate-source charge (Note 4,5)	$Q_{gs}$		-	4	-	
Gate-drain charge (Note 4,5)	$Q_{gd}$		-	7.6	-	

## Source-Drain Diode Ratings and Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	$I_S$	Integral reverse diode in the MOSFET	-	-	3	A
Source current (Pulsed)	$I_{SM}$		-	-	12	A
Forward voltage	$V_{SD}$	$V_{GS}=0\text{V}$ , $I_S=3\text{A}$	-	-	1.5	V
Reverse recovery time (Note 4,5)	$t_{rr}$	$I_S=3\text{A}$ , $V_{GS}=0\text{V}$ $di_F/dt=100\text{A}/\mu\text{s}$	-	372	-	ns
Reverse recovery charge (Note 4,5)	$Q_{rr}$		-	1.8	-	$\mu\text{C}$

Note:

1. Repeated rating: Pulse width limited by safe operating area
2.  $L=42\text{mH}$ ,  $I_{AS}=3\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$
3.  $I_{SD}\leq 3\text{A}$ ,  $di/dt\leq 200\text{A}/\mu\text{s}$ ,  $V_{DD}\leq BV_{DSS}$ , Starting  $T_J=25^\circ\text{C}$
4. Pulse test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature typical characteristics

## Electrical Characteristic Curves

Fig. 1  $I_D - V_{DS}$

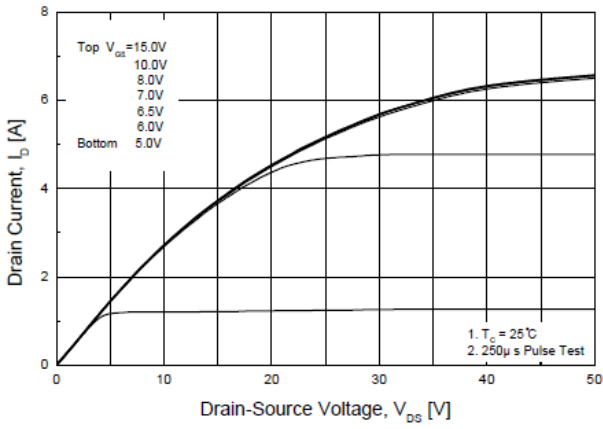


Fig. 2  $I_D - V_{GS}$

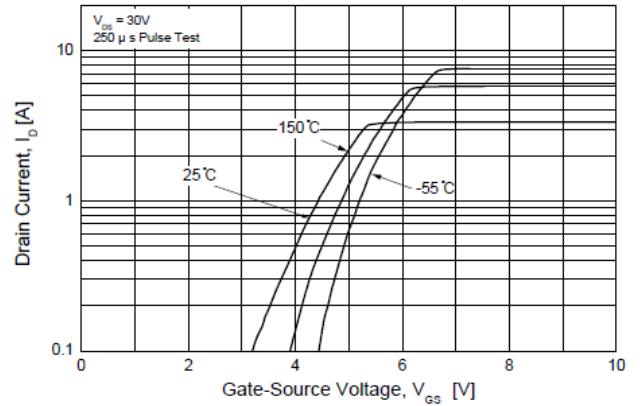


Fig. 3  $R_{DS(ON)} - I_D$

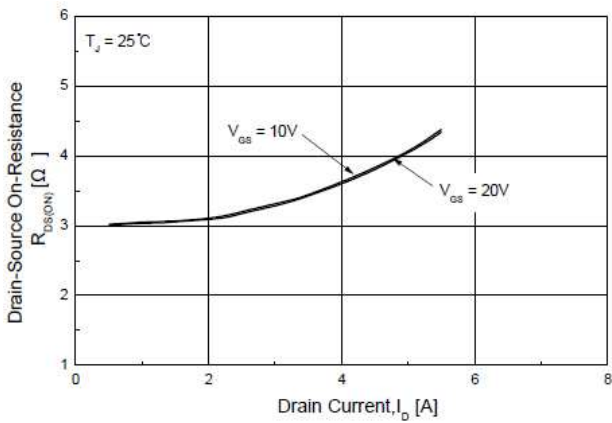


Fig. 4  $I_{DR} - V_{SD}$

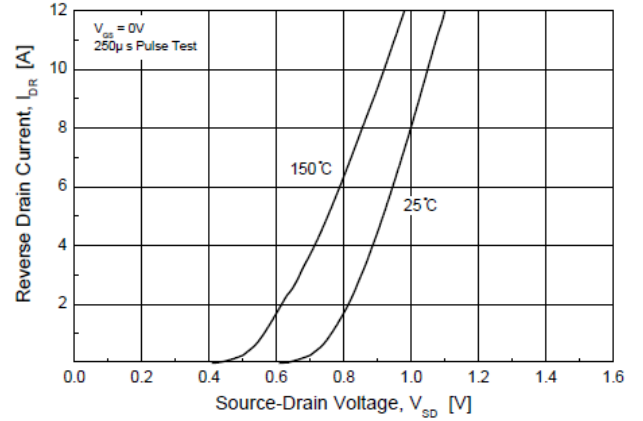


Fig. 5 Capacitance -  $V_{DS}$

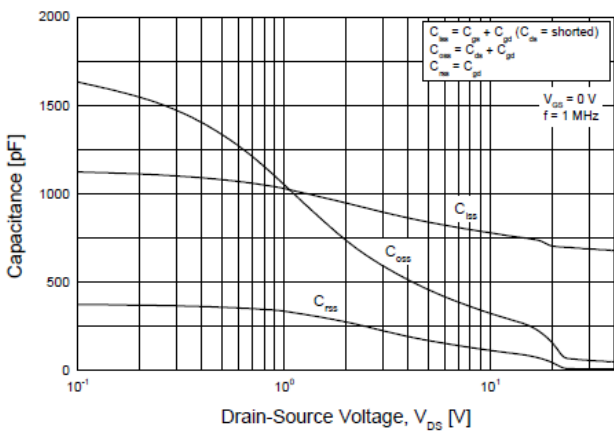
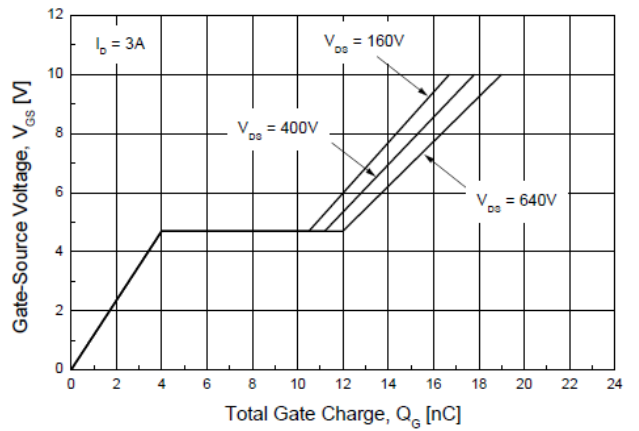


Fig. 6  $V_{GS} - Q_G$



## Electrical Characteristic Curves (Continue)

Fig. 7  $BV_{DSS} - T_J$

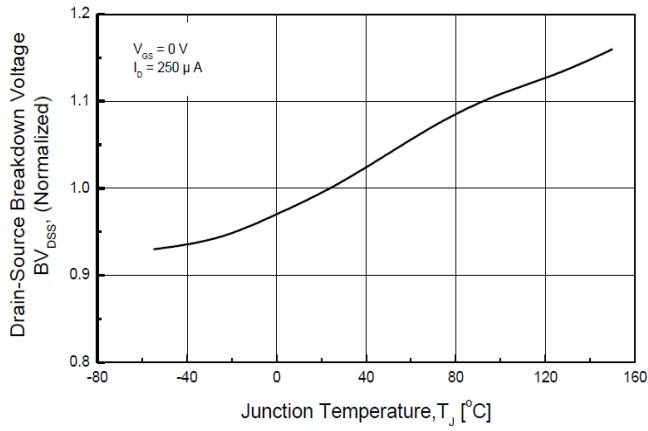


Fig. 8  $R_{DS(ON)} - T_J$

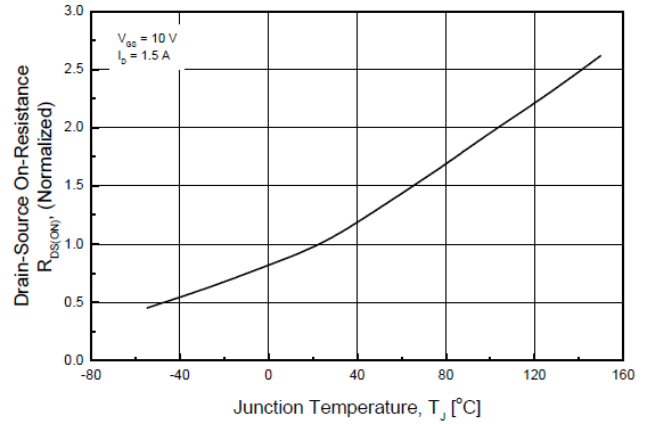


Fig. 9  $I_D - T_C$

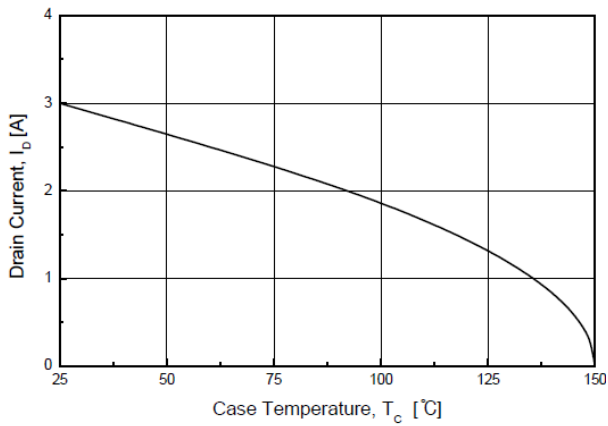


Fig. 10  $V_{GS(th)} - T_J$

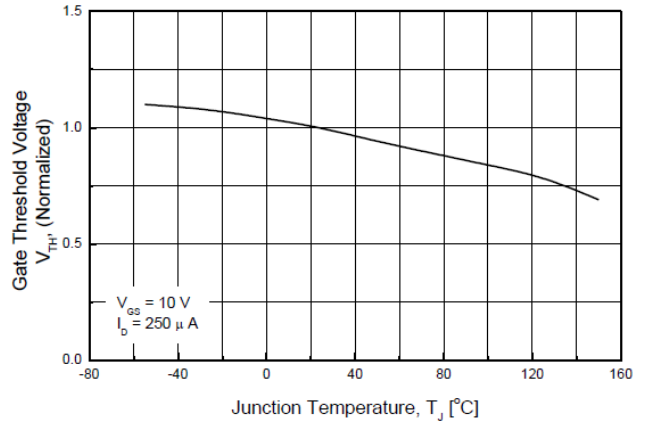


Fig. 11 Safe Operating Area

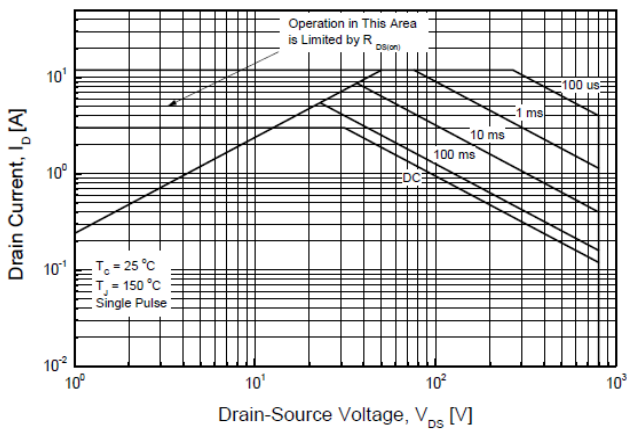


Fig. 12  $Z_{th(j-c)} - t$

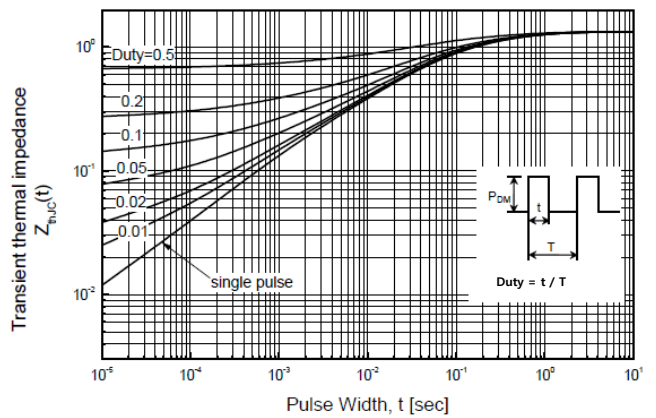


Fig. 13 Gate Charge Test Circuit & Waveform

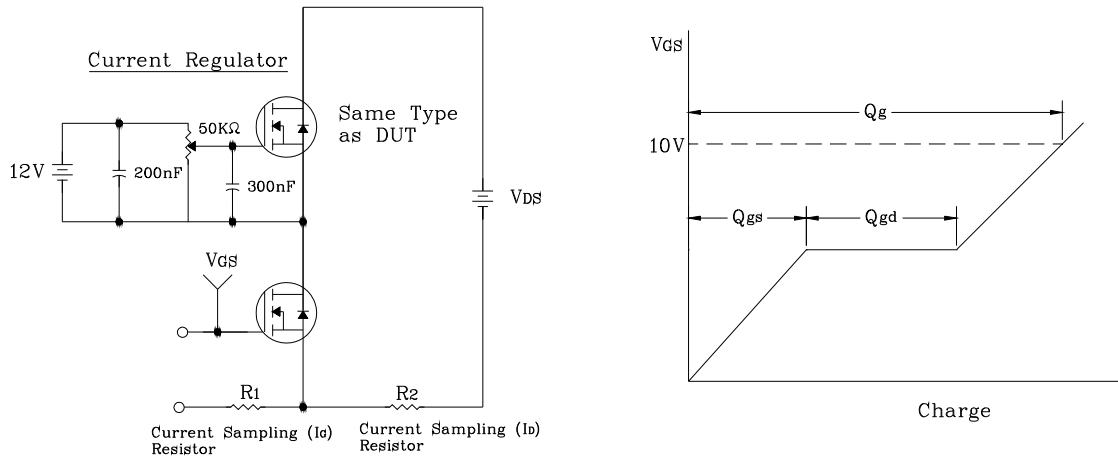


Fig. 14 Resistive Switching Test Circuit & Waveform

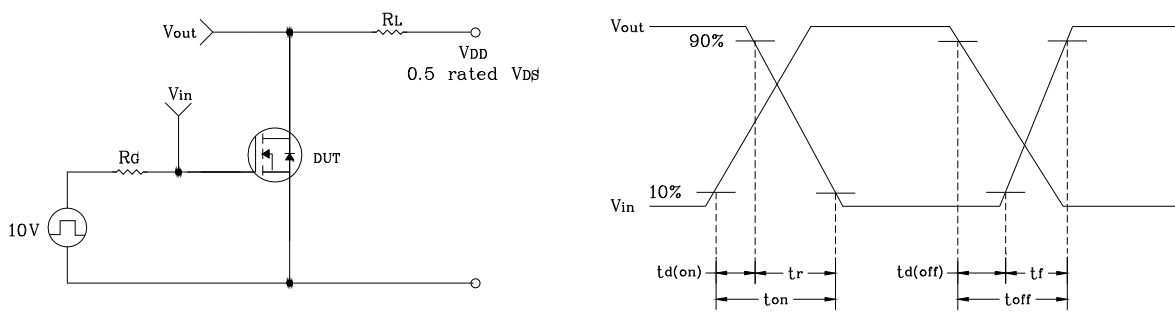


Fig. 15 E<sub>AS</sub> Test Circuit & Waveform

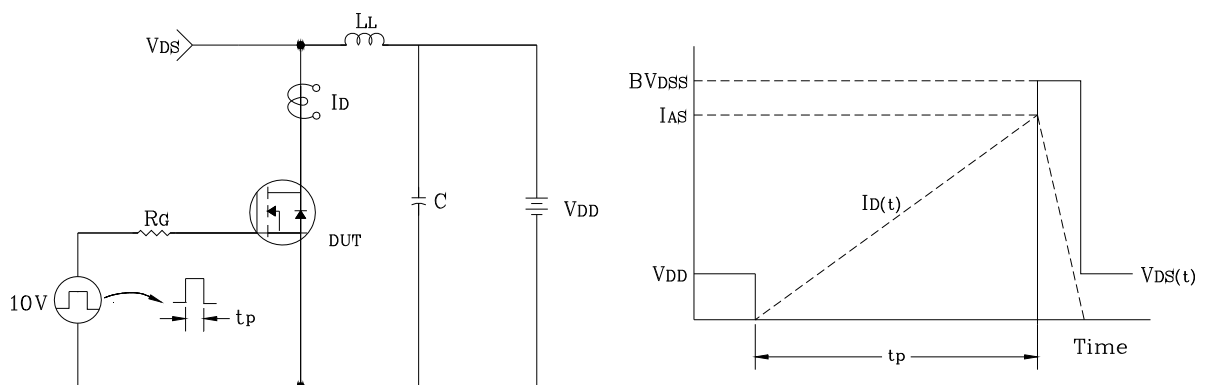
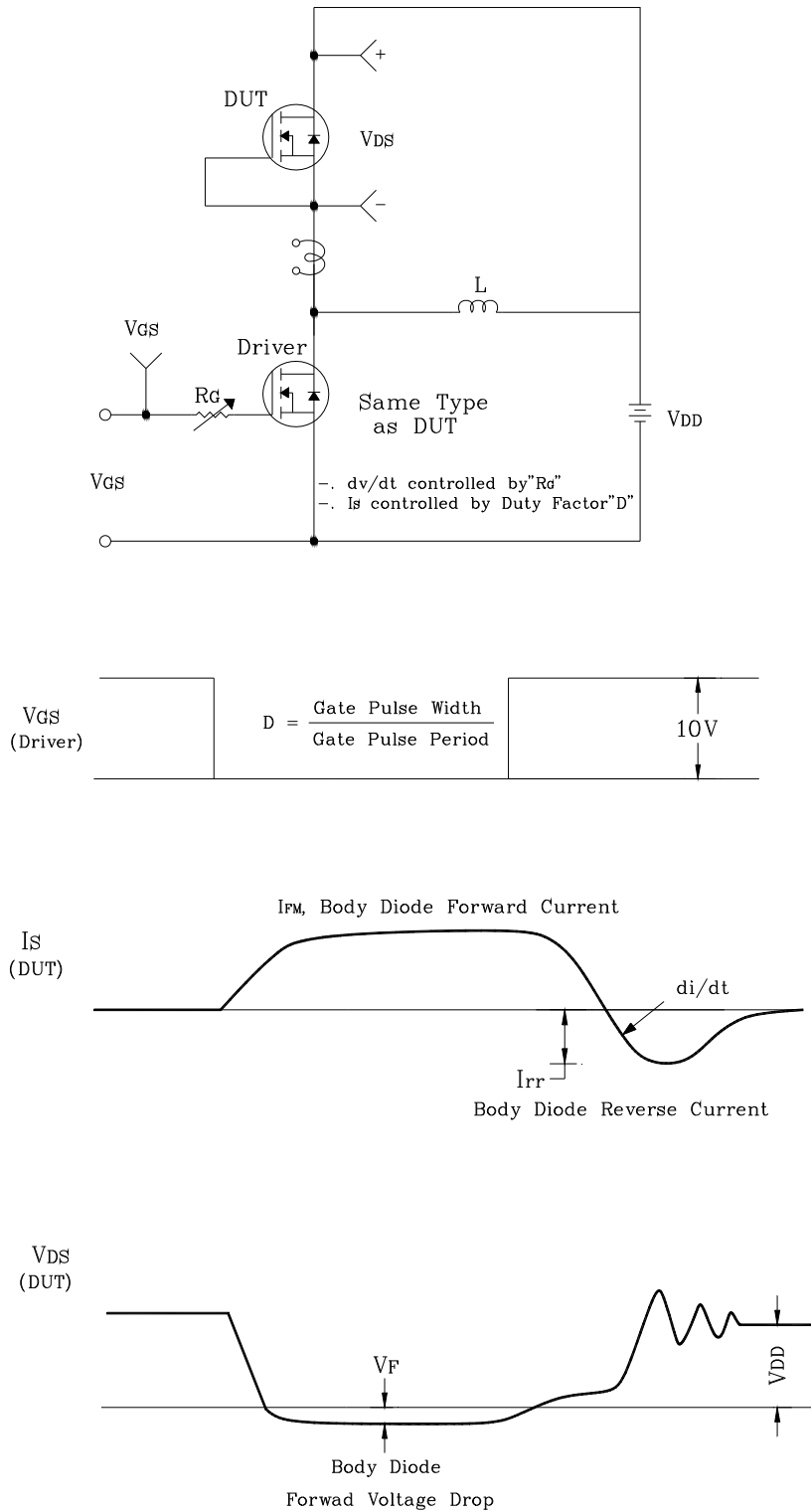
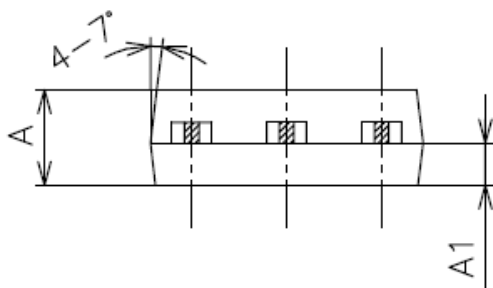
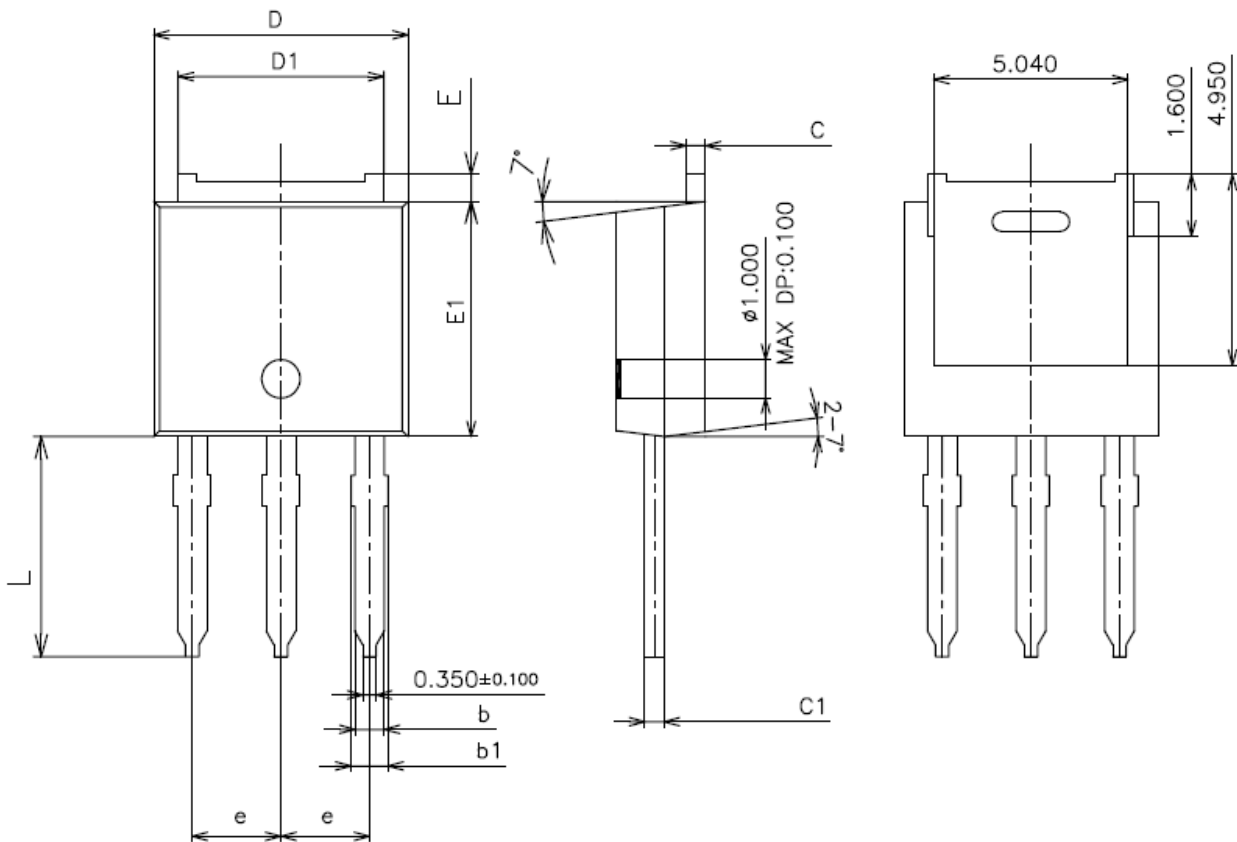


Fig. 16 Diode Reverse Recovery Time Test Circuit & Waveform



## Package Outline Dimensions



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
D	6.40	6.60	6.80	
D1	5.14	5.34	5.54	
E	0.50	0.70	0.90	
E1	5.90	6.10	6.30	
A	2.20	2.30	2.40	
A1	0.87	1.07	1.27	
C	0.40	0.50	0.60	
C1	0.40	0.50	0.60	
L	5.50	5.70	5.90	
b	0.66	0.76	0.86	
b1	0.96 MAX			
e	2.10	2.30	2.50	

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